

FIG. 1 is a perspective view of a device 10. The device 10 includes a substrate 22 having a top surface 28 and a bottom surface 26. A layer 24 is disposed on the top surface 28 of the substrate 22. The layer 24 includes a plurality of regions 25 and 27. The regions 25 are separated by the regions 27. The regions 25 are doped with a first dopant, and the regions 27 are doped with a second dopant. The device 10 is used for the production of a semiconductor device.

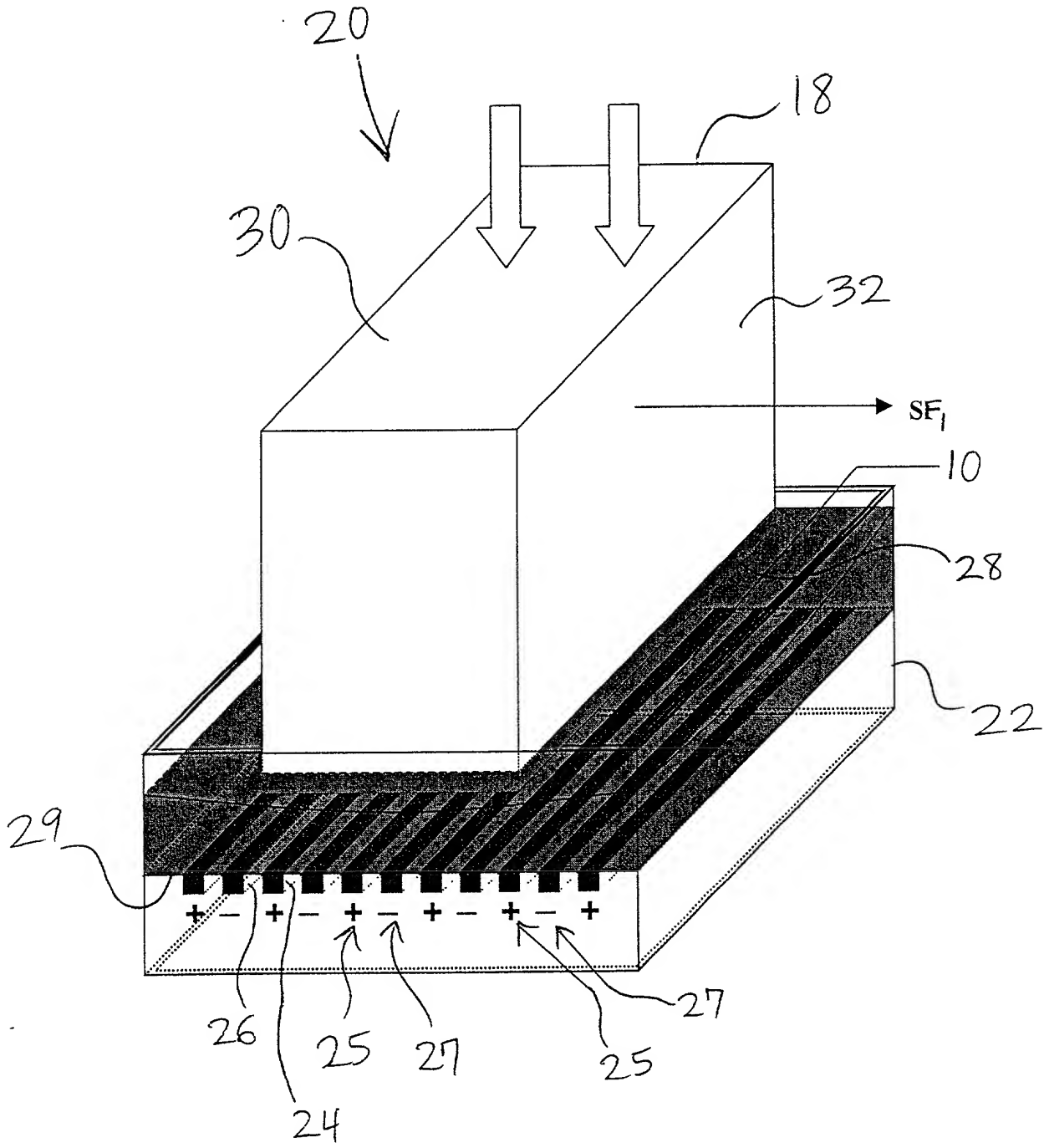


FIG. 1

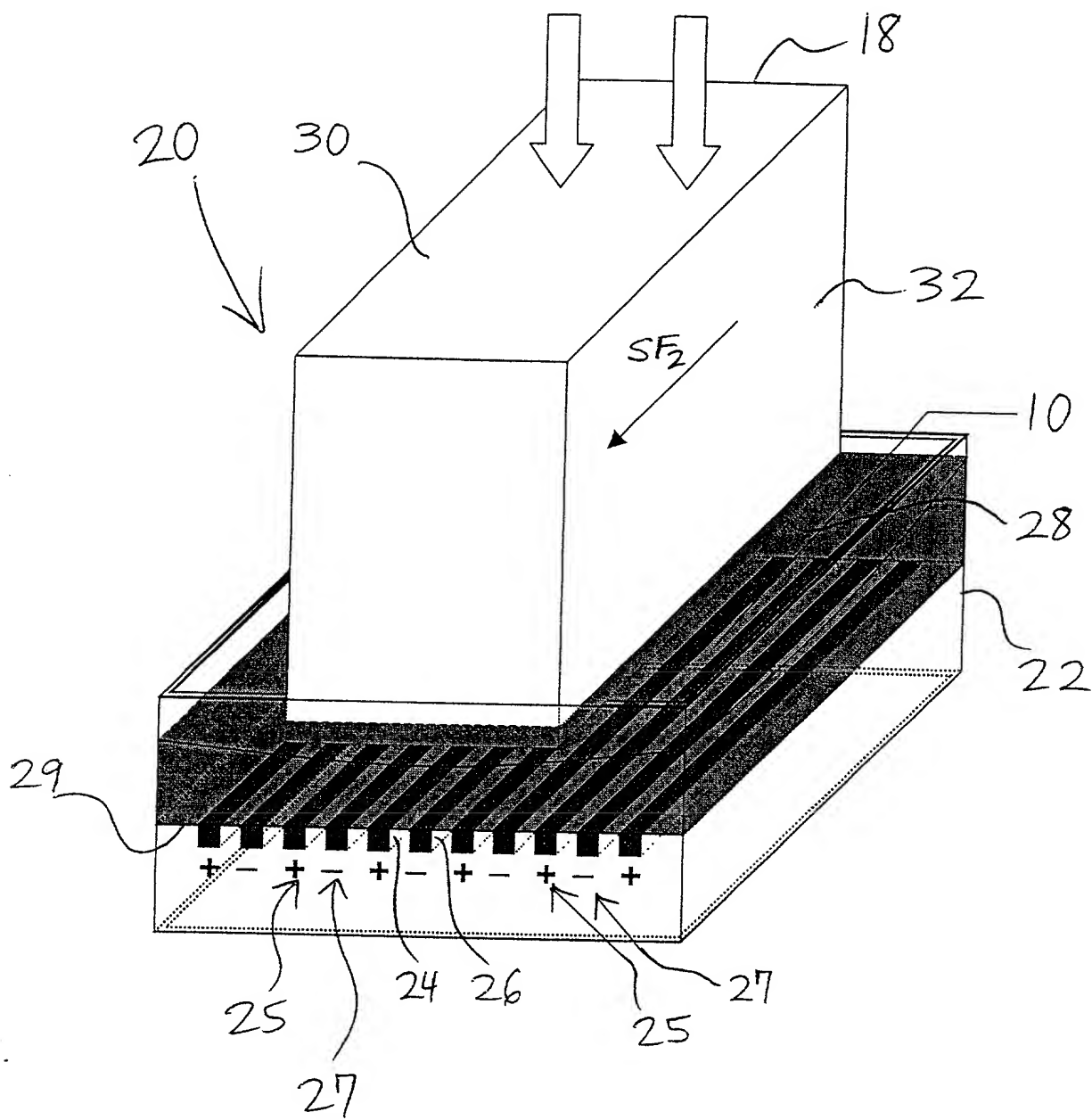


FIG. 2

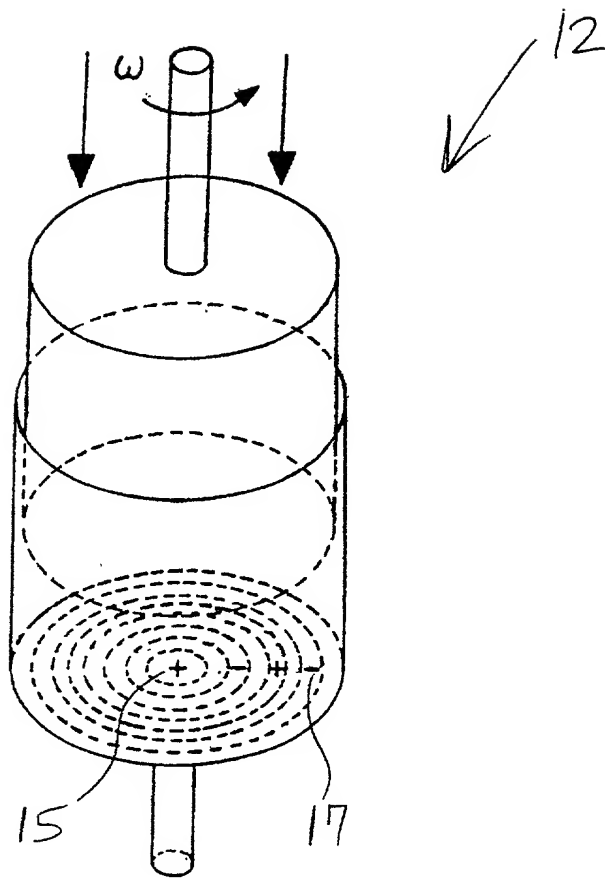


FIG. 3

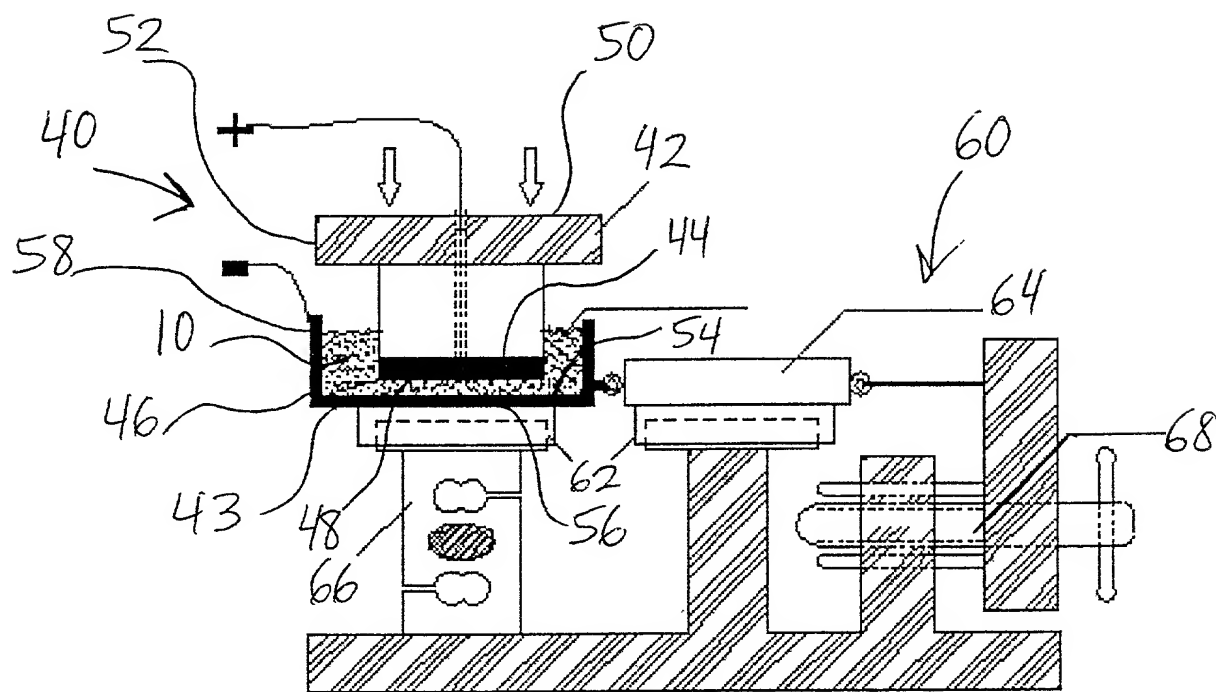


FIG. 4

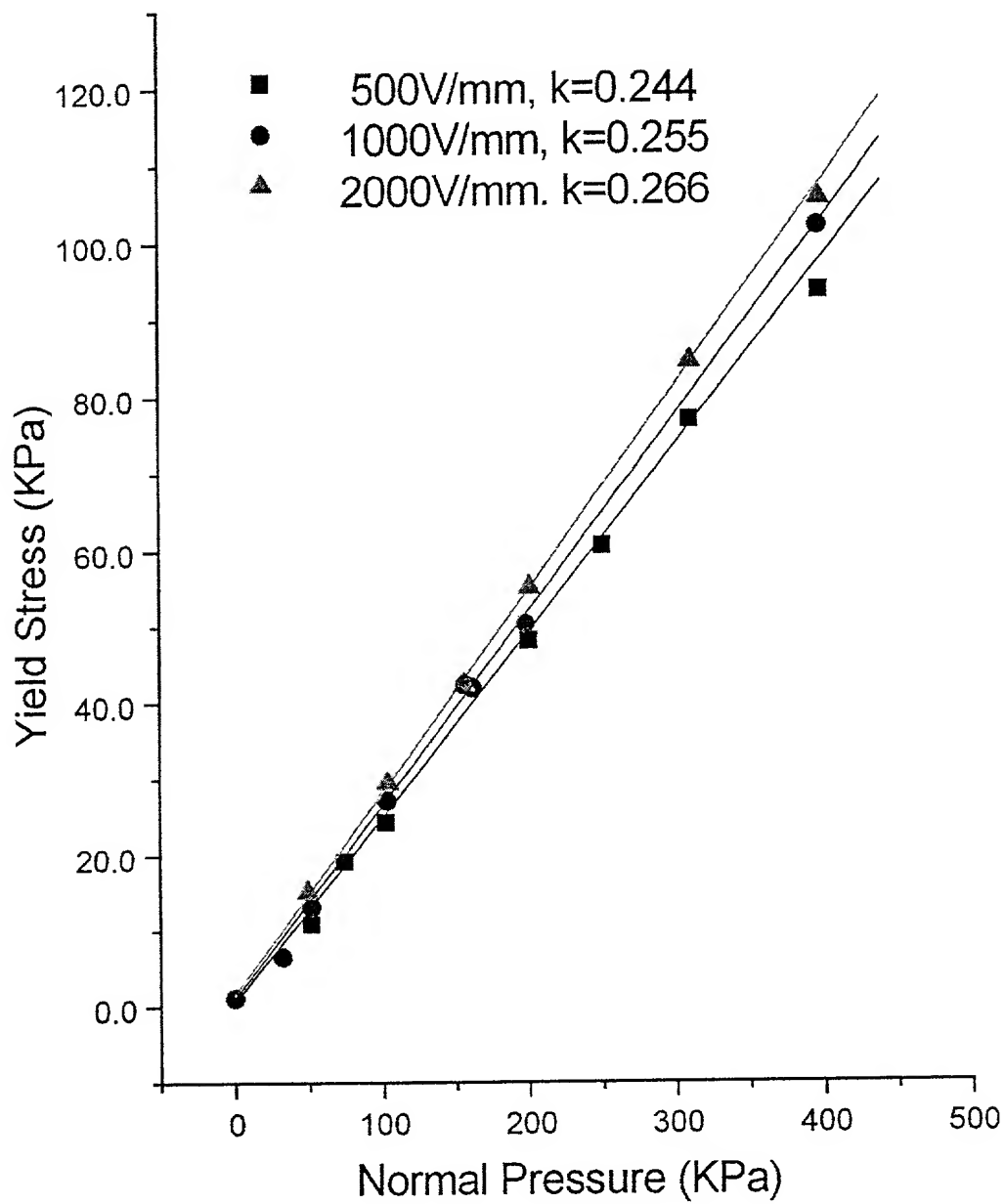


FIG. 5

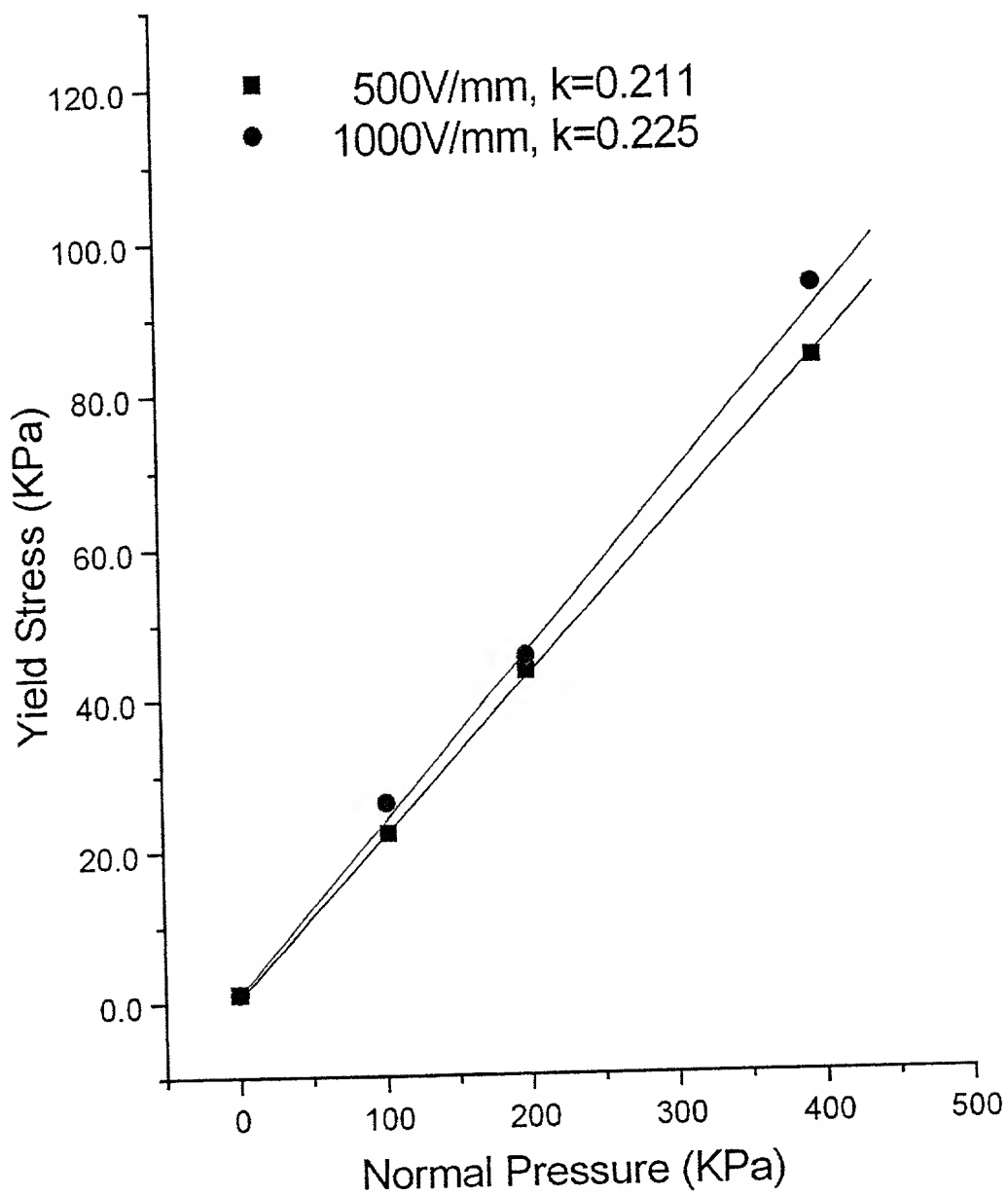


FIG. 6

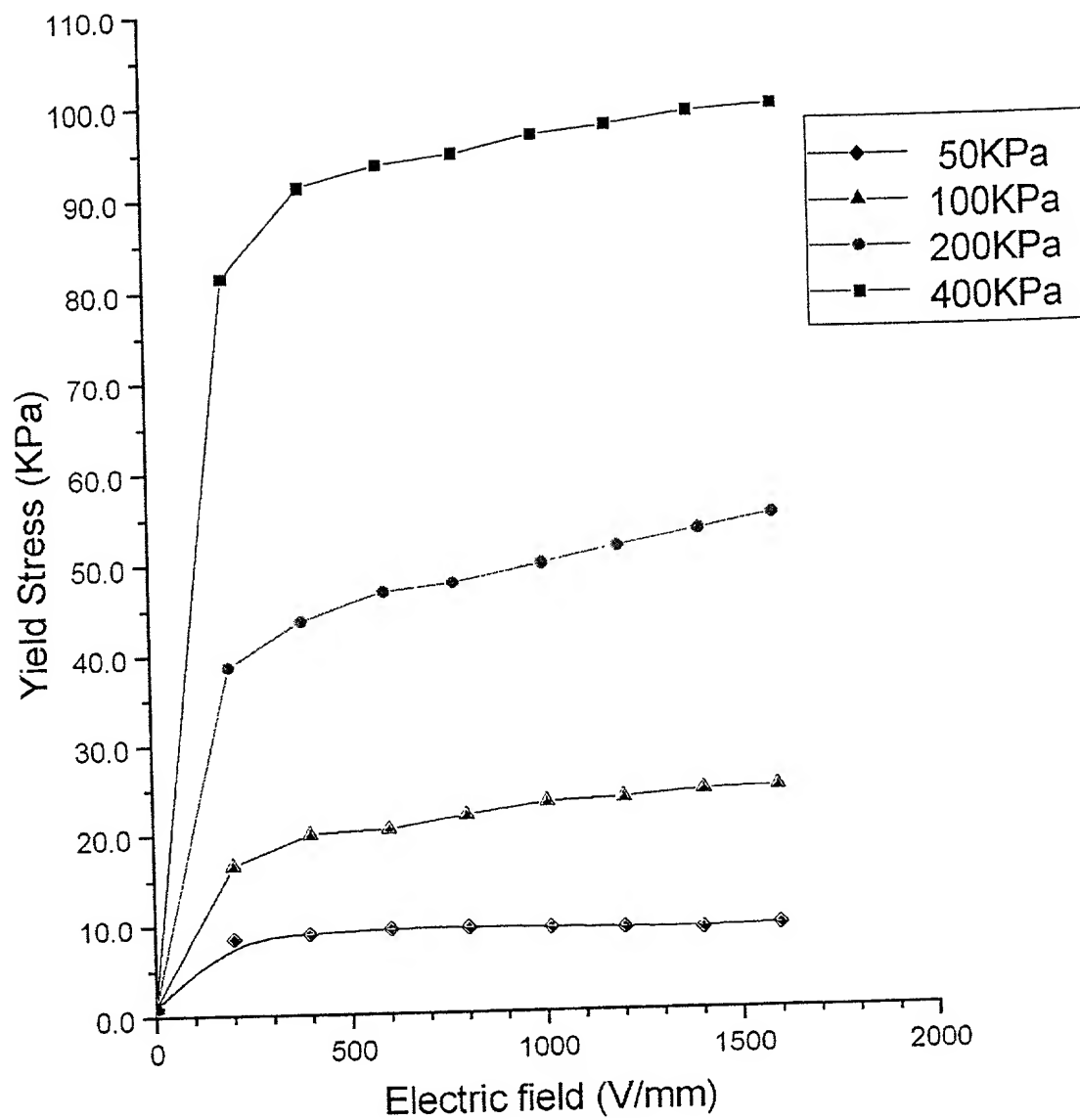


FIG. 7

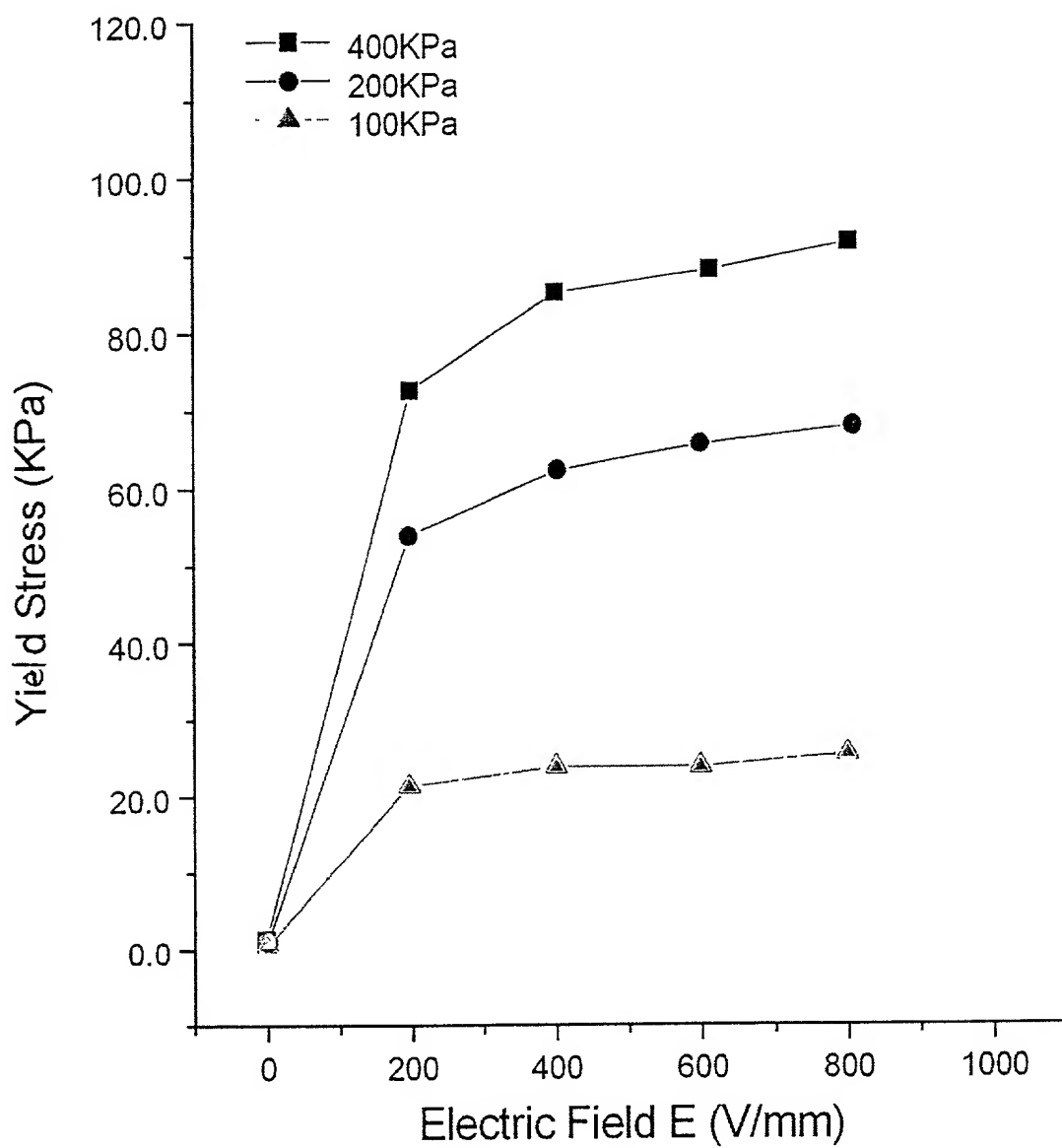


FIG. 8



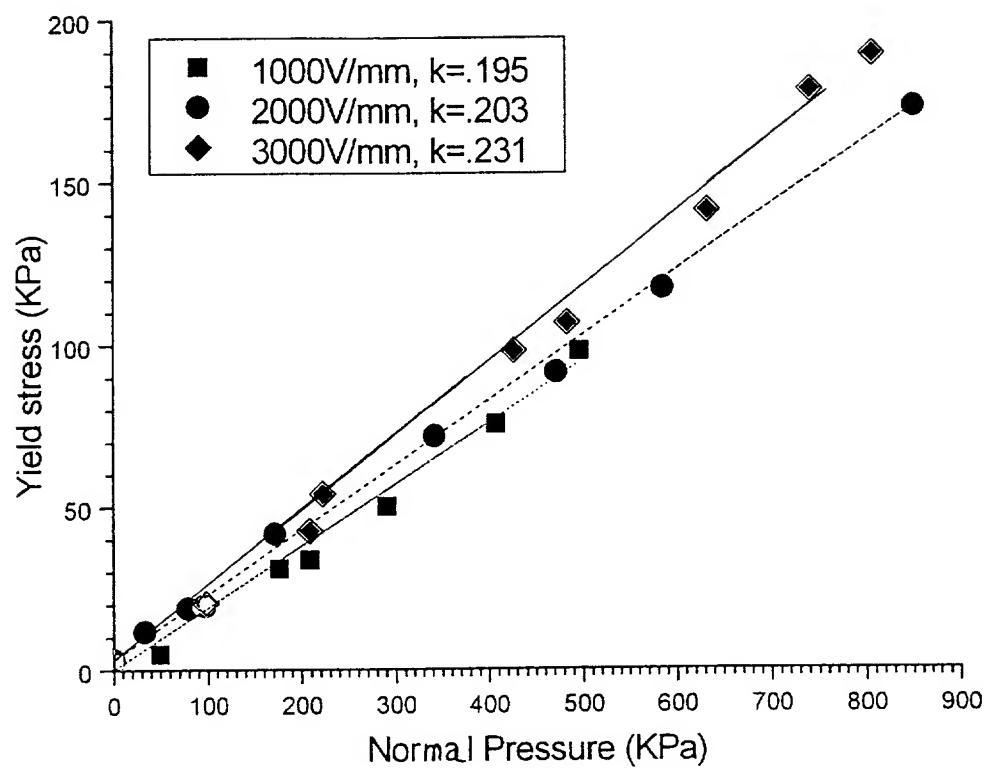


FIG. 9

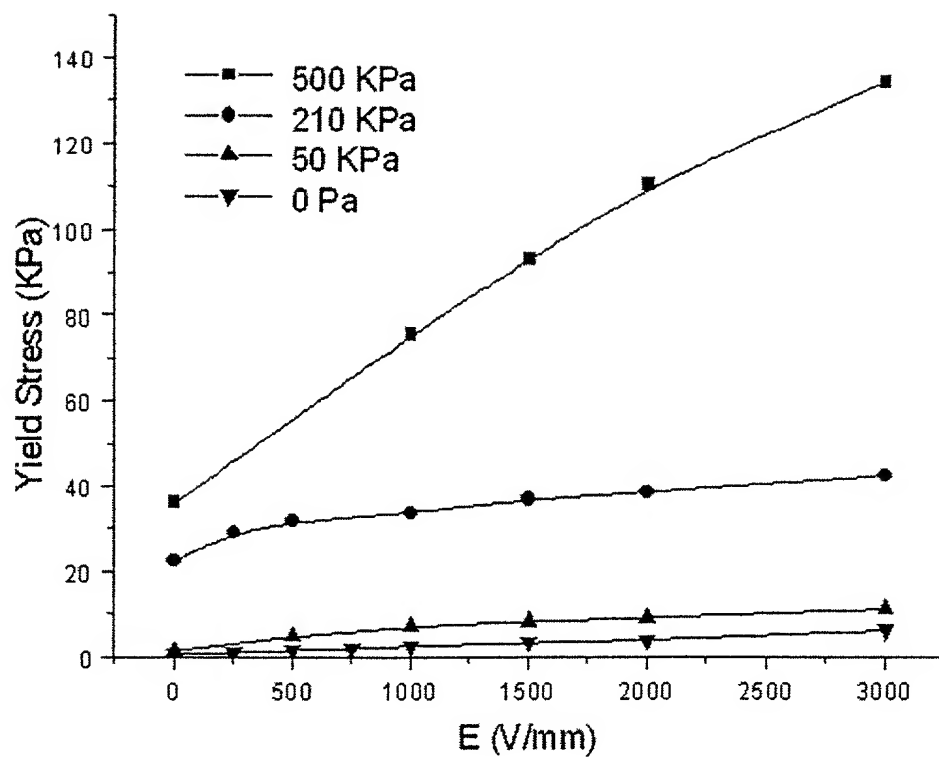


FIG.10